

L Number	Hits	Search Text	DB	Time stamp
1	2693	257/295,298,314,326.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:01
2	67553	phase near chang\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:51
3	32	(phase near chang\$5) and 257/295,298,314,326.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:12
4	408574	257/\$.ccls. 438/\$.ccls. 365/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:13
5	2398	(257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (phase near chang\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:14
6	6	((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (phase near chang\$5)) and (buffer near5 (phase near chang\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:17
7	110	((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (phase near chang\$5)) and (buffer near2 (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:52
9	3	((((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (phase near chang\$5)) and (buffer near2 (layer film)))) and electrode\$1) and plug\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:59
8	79	((((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (phase near chang\$5)) and (buffer near2 (layer film)))) and electrode\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:21
10	1201	(phase near chang\$5) with electrode\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 18:05
11	45	((phase near chang\$5) with electrode\$1) and (buffer near2 (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:58
13	316	((phase near chang\$5) with electrode\$1) and ((insulat\$3 buffer) near2 (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:59

14	30	((phase near chang\$5) with electrode\$1) and ((insulat\$3 dielectric buffer) near2 (layer film))) and plug\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 18:08
15	20	((phase near chang\$5) with electrode\$1) and (thermal near expansion near coefficient)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 17:08
12	412	((phase near chang\$5) with electrode\$1) and ((insulat\$3 dielectric buffer) near2 (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 18:08
16	6	("4115872"   "4203123"   "4809044"   "5166758"   "5177567"   "5510629").PN.	USPAT	2004/09/03 17:38
17	6	("3611063"   "3846767"   "4599705"   "4804490"   "4809044"   "4845533").PN.	USPAT	2004/09/03 17:44
18	6	("3271591"   "3699543"   "3918032"   "4177475"   "4203123"   "4845533").PN.	USPAT	2004/09/03 17:44
19	4509	((phase near chang\$5) chalcogenide) with (conduct\$3 electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 18:08
20	1159	((phase near chang\$5) chalcogenide) with (conduct\$3 electrode\$1)) and ((insulat\$3 dielectric buffer) near2 (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 18:08
21	158	((phase near chang\$5) chalcogenide) with (conduct\$3 electrode\$1)) and ((insulat\$3 dielectric buffer) near2 (layer film))) and plug\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 18:09
22	4	("5705430"   "5789277"   "5831276"   "5841150").PN.	USPAT	2004/09/03 18:21